

**South Dakota School of Mines & Technology**  
**Electronic, Magnetic, & Optical Properties of Materials, Spring 2026**  
**EE 362-M01 3 credits**

### **Instructor Information**

**Instructor's Name-** Thomas Montoya

**Instructor's Contact Information-** (605) 394-1219, [Thomas.Montoya@sdsmt.edu](mailto:Thomas.Montoya@sdsmt.edu), EEP 314

**Instructor Office Hours-** 8:30-9:30 am MWF & 4-5 pm MF, or when available (open door policy).

As I do not always notice voicemails in a timely fashion, e-mails or in person are the preferred contact methods. Unless I am traveling or it arrives at night, I typically respond to e-mails the same day.

### **Course Information**

**Course Start/End Dates-** 1/12/2026 to 5/8/2026.

**Course Final Exam Date and Time -** Friday, May 8, 2026 from 2-3:50 pm

**Course Meeting Times and Location-** MWF from 12-12:50 pm in EEP 208

**Course Delivery Method-** The course will be delivered in-person for lectures, quizzes, and exams. The syllabus and a link to my web page <http://montoya.sdsmt.edu> will be posted on D2L. The course web page will be used for posting assignments, examples, solutions, etcetera. E-mail will be used to notify students of course-related information and events (**check daily**). Your [first.last@Mines.sdsmt.edu](mailto:first.last@Mines.sdsmt.edu) address will be used for these e-mails.

### **Course Description**

This course studies the behavior of materials of interest to electrical engineers and covers fundamental issues such as energy band theory, density of states, Fermi-Dirac statistics, equilibrium statistics in semiconductors, and Fermi energy. This foundation is then used to study topics such as conduction and semiconductor devices. Other topics include Peltier devices, optoelectronics, and piezoelectric devices.

**Course Prerequisites-** MATH 225, MATH 321 with a grade of “C” or higher, and (PHYS 213 or PHYS 209)

### **Student Learning Outcomes**

#### **Student Outcomes (SOs)**

Student Outcomes are defined in ABET’s accreditation standards for engineering programs:

1. An ability to identify, formulate, and solve complex engineering problems by applying principles of engineering, science, and mathematics.
2. An ability to apply engineering design to produce solutions that meet specified needs with consideration of public health, safety, and welfare, as well as global, cultural, social, environmental, and economic factors.
3. An ability to communicate effectively with a range of audiences.
4. An ability to recognize ethical and professional responsibilities in engineering situations and make informed judgments, which must consider the impact of engineering solutions in global, economic, environmental, and societal contexts.

5. An ability to function effectively on a team whose members together provide leadership, create a collaborative and inclusive environment, establish goals, plan tasks, and meet objectives.
6. An ability to develop and conduct appropriate experimentation, analyze and interpret data, and use engineering judgment to draw conclusions.
7. An ability to acquire and apply new knowledge as needed, using appropriate learning strategies.

## **Course Learning Outcomes (CLOs)**

Upon completion of this course, students should demonstrate the ability to:

- A. Describe the physical structure of semiconductor materials. (SO 1)
- B. Understand the basic concepts describing the behavior of bulk semiconductors, including the energy-band model, the Fermi function, and the calculation of electron and hole densities in semiconductors. (SO 1)
- C. Understand the roles played by diffusion current, drift current, and generation-recombination in describing current flow in semiconductors. (SO 1)
- D. Describe the electric fields and electric potential inside a pn junction. (SO 1)
- E. Understand the operation of, and terminology used in describing and specifying the properties of MOS capacitors. (SO 1)
- F. Understand the operation of, and terminology used in describing and specifying the properties of MOSFETs. (SO 1)
- G. Understand the operation of, and terminology used in describing and specifying the properties of BJTs. (SO 1)
- H. Understand operation of, and applications for piezoelectric & thermoelectric devices as well as understand dissimilar metal corrosion and means for preventing it. (SOs 1 & 7)

**Course Topics-** See course description and tentative course schedule.

## **Course Materials**

### **Required Textbook(s) and Materials**

Semiconductor Physics and Devices: Basic Principles (4<sup>th</sup> Edition), Donald A. Neamen, McGraw Hill, 2012, ISBN 978-0-07-352958-5.

### **Technology Equipment and Skills Needed for the Course**

The course requires use of a computer and scientific calculator (capable complex number operations). Software needed/used in the course will include a pdf reader (Acrobat), D2L, MATLAB and/or MathCad, Microsoft Office, and possibly Zoom. Skills required include the ability to navigate D2L and internet, upload/download files (e.g., text and pdf files), use MS Office programs, communicate via email, use MATLAB and/or MathCad, and use Zoom (possibly).

## **Course Grading**

### **Coursework**

- Course instruction will be delivered in lectures. Assignments will be posted to <http://montoya.sdsmt.edu>.
- Bring notes, text, and calculator to every class. Most quizzes will be unannounced and require a calculator and might be open book/notes (no borrowing/sharing, smartphones, or computers).

- To aid grading, homework shall meet the following specifications (example on course web page):
  - (a) Use the front (i.e., single-sided) of 8.5" × 11" engineering graph paper or plain white paper (NO pages torn from spiral notebooks) for assignments. Hardcopy only!
  - (b) At the top of **each** page put date, course number, your name, and page numbering (i.e., page  $x$  of  $y$  or  $x/y$  formats in upper right-hand corner). Ensure problems & pages are in order.
  - (c) All work exceeding one page should be stapled - no paper clips, folded corners, or folders.
  - (d) Write-out problem numbers & descriptions, copy/draw figures, and **show all** work so it can be understood without the text. No work (i.e., "magic" answer) → no credit.
  - (e) Writing/figures/graphs must be legible and large enough to read → illegible = no credit.
  - (f) Reference equations derived in the text (e.g., equation number and/or page number). Fundamental equations (e.g., Maxwell's equations, Ohm's Law ...) are excluded from this requirement.
  - (g) Use notation, especially for vectors, and conventional engineering units & prefixes (i.e., MKS) as given in class and text. For example,  $\bar{E} = \hat{a}_\theta 10 \text{ kV/m}$  and 100 MHz **NOT**  $\bar{E} = \hat{\theta} 100 \text{ V/cm}$  and  $10^5 \text{ kHz}$ . Answers with incorrect notation and/or without applicable units are incomplete/incorrect.
  - (h) Answers should be boxed/double underlined, in **decimal** format if numeric (no fractions) with variables, values & units (if any) included. Also, use lead zeros for fractional answers. For example, " $V_x = 0.4 \text{ V}$ " **not** " $V_x = .4$ " or " $V_x = 2/5 \text{ V}$ ". Typically, 4-6 significant digits are used.
  - (i) Work problems sequentially in a **single** vertical column with subparts clearly labeled, e.g., a), b) ... Leave space (~1/2") between consecutive parts of a problem, and draw a line across the page at the end of each problem if there is more than one. No 'checker boarding.'
  - (j) **No** more than **two** problems on any single page.

### Attendance Policy

Excused absences will be handled in accordance with [South Dakota Mines Policy 3-1](#). Attendance is required. Notify instructor in advance (when possible) if you will be absent from class.

### Late/Make-up Assignment Policy

- Homework (HW) is due in hardcopy form at the beginning of class on the specified days (up to 20% penalty for being late). SDM Policy 3-1 will usually not apply as HW assignments are given at least 3 business days in advance. If you know that you will be missing a class, it may be turned in early. HW will **not** be accepted or graded after solutions are posted on the course web page.
- Missed quizzes will **not** be made up for unexcused absences. See SDM Policy 3-1 for excused absences.
- If 2/3 of quizzes and 2/3 of HW are completed at a **passing** level and **no** excused make-up quizzes are taken, the lowest HW grade and lowest two quiz grades will be dropped (no questions asked). If not, **all** quizzes and HW will count (no drops).

### Academic Integrity

South Dakota Mines is committed to academic honesty and scholarly integrity. The South Dakota Board of Regents [\(BOR\) Policy 2.9.2](#) provides a comprehensive definition of "Academic Dishonesty", which include cheating and plagiarism. All Instructors at South Dakota Mines are required to report allegations of academic misconduct to the Student Conduct Officer. [BOR Policy 3.4.1](#) provides detailed information regarding key definitions, policy information, prohibited conduct, and the Student Conduct process adhered to at South Dakota Mines. Any student suspected of violating academic integrity standards will be reported in accordance with the process outlined on the South Dakota Mines [website](#).

- Students are encouraged to discuss homework with classmates in general terms. However, copying, plagiarism ... is not acceptable and will be penalized (e.g., grade of zero).

## Grading and Assessment

Student learning is assessed by a combination of exams, quizzes, and homework.

| Description                       | Percent     |
|-----------------------------------|-------------|
| Three (3) Hourly exams @ 15% each | 45%         |
| Quizzes                           | 20%         |
| Homework                          | 15%         |
| Final exam                        | 20%         |
| <b>Total</b>                      | <b>100%</b> |

**Special Note Regarding Final Exams:** Per South Dakota Mines Policy (2-8), if you are scheduled to take three or more final/last exams on the same day during finals week, you may request that the middle exam(s) of the day be rescheduled. ***You are required to make this request of your Instructor(s) at least 30 days prior to the last day of regular classes.***

Grading Scale- 100 > A > 90, 89 > B > 80, 79 > C > 70, 69 > D > 60, F < 60.

## Academic Freedom Statement

Academic Freedom is the cornerstone upon which higher education is built. Academic freedom, as defined by [BOR Policy 1.6.1](#), is fundamental to the advancement of truth, development of critical thinking, promotion of civil discourse, and contribution to the public good. Each course includes the freedom to discuss relevant matters and present various scholarly views in the classroom, as determined by the subject-matter expertise of the instructor. Students are encouraged to develop the capacity for critical thinking and to pursue the truth, debate ideas, express and evaluate their opinions, and draw conclusions. Students are free to take reasoned exception to the views offered in any course of study and to reserve judgment about matters of opinion, but they are responsible for learning the content of any course of study for which they are enrolled.<sup>1</sup>

<sup>1</sup>*Language adapted from the American Association of University Professors "Joint Statement on Rights and Freedoms of Students".*

## Complaint Process

While we hope that every student has a meaningful and positive experience at South Dakota Mines, should a concern arise, students are encouraged to first attempt to resolve their concern directly with the person or office directly involved. Following that attempt, should the concern remain unresolved, students are encouraged to reach out to the Dean of Students office at [DeanOfStudents@sdsmt.edu](mailto:DeanOfStudents@sdsmt.edu) or 605.394.2416. Additionally, students may access the [online form](#) to submit their complaint, appeal, or grievance.

## Grade Appeal Policy

In alignment with [BOR Policy 2.9.1](#) and [SDSMT Policy 2-21](#), students who wish to appeal their final course grade shall first discuss the matter with the course instructor. If the concerns are unresolved following that discussion, students may appeal to the instructor's department head or supervisor for a decision. If the student is dissatisfied with the supervisor decision, the student may then utilize the [online form](#) to submit "Appeal – Academic" for a "Grade Dispute".

## **Opportunity for All - Student Success Services and Support**

Students are provided a one-stop source for information regarding all the services and supports to ensure success. Visit the [Opportunity Center](#) page to learn more.

## **Accessibility Accommodations**

If you have a disability for which you are or may be requesting an accommodation, you are encouraged to contact both your instructor and the Accessibility Services office at 605.394.2533 or [DisabilityServices@sdsmt.edu](mailto:DisabilityServices@sdsmt.edu) as early as possible in the semester.

## **South Dakota Board of Regents Required Syllabus Statements**

The following statements may be found online in South Dakota Board of Regents Academic Affairs Council Guideline [2.7.3.A\(1\)](#):

- Freedom in Learning
- Americans with Disabilities Act
- Academic Dishonesty and Misconduct
- Acceptable Use of Technology
- Emergency Alert Communications

## **Electronic Devices Policy**

Please silence/turn off your cell phone before class starts. No text messaging or headphones in class. You may use a laptop/tablet in class for purposes of note taking (NOT allowed for exams or quizzes). No other use of any other electronic/computer media, other than calculators, is allowed during class time.

## **Generative Artificial Intelligence Tool Utilization**

To fully support the development of your independent thinking and creativity in this course, the use of generative Artificial Intelligence (genAI) tools is not allowed. Given the nature of the course, it is doubtful genAI would be of any significant use.

**Topics/Course Schedule:** Selected topics from Chapters 1-8, 10, and 12, supplemented by notes. See attached tentative schedule.

| Class   Date   | Tentative Topics/Activities   | Reading/Text   |
|--|---|--|
| 1   1/12/26<br>2   1/14/26<br>3   1/16/26                    | <b>The Crystal Structure of Solids-</b> Semiconductor Materials, types of solids, space lattices, diamond structure, and atomic bonding. Time allowing- imperfection & impurities in solids               | <ul style="list-style-type: none"> <li>• 1.0 - 1.3</li> <li>• 1.3</li> <li>• 1.4 - 1.6</li> </ul>                            |
| 1/19/26  | <b>Holiday</b>  |  |
| 4   1/21/26<br>5   1/23/26<br>6   1/26/26                    | <b>Introduction to Quantum Mechanics-</b> Principles of Quantum Mechanics, Schrodinger's Wave Equation, Applications of Schrodinger's Wave Equation, Extensions of the Wave Theory to Atoms               | <ul style="list-style-type: none"> <li>• 2.0 - 2.2</li> <li>• 2.2 - 2.3</li> <li>• 2.3 - 2.4</li> </ul>                      |
| 7   1/28/26<br>8   1/30/26<br>9   2/2/26<br>10   2/4/26      | <b>Introduction to the Quantum Theory of Solids</b> – allowed & forbidden energy bands, electrical conduction in solids, extension to three dimensions, density of states function, statistical mechanics | <ul style="list-style-type: none"> <li>• 3.0 - 3.1</li> <li>• 3.2</li> <li>• 3.3 - 3.4</li> <li>• 3.4 - 3.5</li> </ul>       |
| 11   2/6/26<br>12   2/9/26<br>13   2/11/26                   | <b>The Semiconductor in Equilibrium-</b> charge carriers, dopant atoms and energy levels, extrinsic semiconductor, statistics of donors and acceptors, charge neutrality, position of Fermi energy level  | <ul style="list-style-type: none"> <li>• 4.0 - 4.1</li> <li>• 4.2 - 4.3</li> <li>• 4.4 - 4.6</li> </ul>                      |
| 14   2/13/26   | <b>Exam #1-</b> Covers material from Chapters 1 - 3   |  |
| <b>2/16/26</b>   | <b>Holiday</b>  |  |
| 15   2/18/26<br>16   2/20/26<br>17   2/23/26                 | <b>Carrier Transport Phenomena-</b> carrier drift, carrier diffusion, graded impurity distribution, Hall Effect   | <ul style="list-style-type: none"> <li>• 5.0 - 5.1</li> <li>• 5.1 – 5.3</li> <li>• 5.3 – 5.4</li> </ul>                      |
| 18   2/25/26<br>19   2/27/26<br>20   3/2/26<br>21   3/4/26   | <b>Nonequilibrium Excess Carriers in Semiconductors-</b> carrier generation & recombination, characteristics of excess carriers, ambipolar transport, quasi-Fermi energy levels                           | <ul style="list-style-type: none"> <li>• 6.0 - 6.1</li> <li>• 6.1 - 6.2</li> <li>• 6.3</li> <li>• 6.3 - 6.4</li> </ul>       |
| 22   3/6/26<br>23   3/9/26                                   | <b>The pn Junction-</b> basic structure of the pn junction, zero applied bias, reverse applied bias   | <ul style="list-style-type: none"> <li>• 7.0 - 7.2</li> <li>• 7.2 - 7.3</li> </ul>   |
| 24   3/11/26   | <b>Exam #2-</b> Covers material from Chapters 4 - 6   |  |
| 25   3/13/26   | reverse applied bias cont., junction breakdown  | • 7.3 – 7.4  |
| <b>3/16 – 3/20</b>   | <b>Spring Break</b>   |  |
| 26   3/23/26<br>27   3/25/26<br>28   3/27/26                 | <b>The pn Diode</b> – pn junction current, generation-recombination currents and high-injection levels, small-signal-model of the pn junction   | <ul style="list-style-type: none"> <li>• 8.0 - 8.1</li> <li>• 8.1 - 8.2</li> <li>• 8.2 - 8.3</li> </ul>                      |
| 29   3/30/26<br>30   4/1/26                                  | <b>Fundamentals of the Metal-Oxide – Semiconductor Field-Effect Transistor-</b> two-terminal MOS structure,   | <ul style="list-style-type: none"> <li>• 10.0 - 10.1</li> <li>• 10.1</li> </ul>  |
| <b>4/3 – 4/6*</b>  | <b>Holiday</b> (* Governor gave Monday as holiday last year)  |  |
| 31   4/8/26<br>32   4/10/26<br>33   4/13/26                  | two-terminal MOS structure cont., capacitance-voltage characteristics, basic MOSFET operation, frequency limitations  | <ul style="list-style-type: none"> <li>• 10.1 - 10.3</li> <li>• 10.3</li> <li>• 10.3 - 10.4</li> </ul>                       |
| 34   4/15/26<br>35   4/17/26<br>36   4/20/26<br>37   4/22/26 | <b>The Bipolar Transistor-</b> bipolar transistor action, minority carrier distribution, transistor currents & low-frequency common-base current gain   | <ul style="list-style-type: none"> <li>• 12.0 - 12.1</li> <li>• 12.1 - 12.2</li> <li>• 12.2 -12.3</li> <li>• 12.3</li> </ul> |
| 38   4/24/26   | <b>Exam #3-</b> Covers material from Chapters 7, 8, and 10  |  |
| 39   4/27/26<br>40   4/29/26<br>41   5/1/26                  | <b>Special Topics-</b> thermoelectric devices, piezoelectric devices, dissimilar metal (galvanic) corrosion, and (time-allowing) optoelectronics  | <ul style="list-style-type: none"> <li>• Notes</li> <li>• Notes</li> <li>• Notes</li> </ul>                                  |
|  | <b>Final Exam- Friday, May 8, 2026 from 2 - 3:50 pm, EEP 208</b>  |  |